



TO-92 Plastic-Encapsulate Transistors

BC347 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM} : 0.3 \text{ W (} T_{amb}=25 \text{)}$$

Collector current

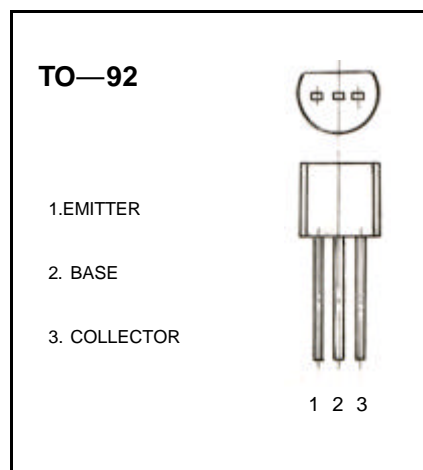
$$I_{CM} : 0.1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 50 \text{ V}$$

Operating and storage junction temperature range

$$T_J , T_{stg} : -55 \text{ to } +150$$

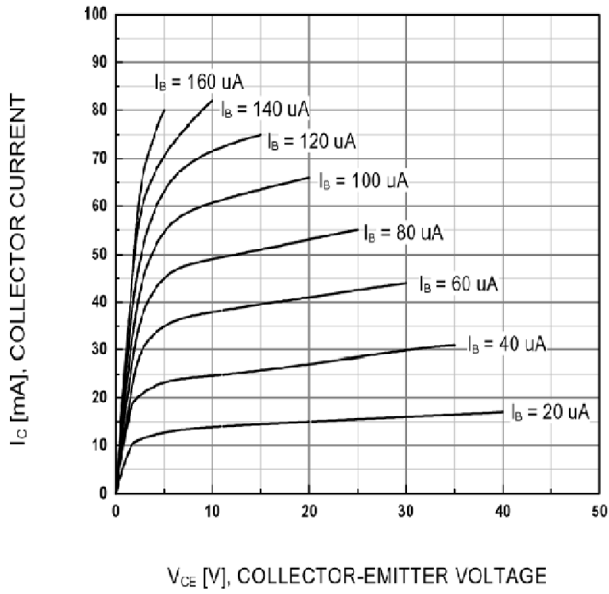


ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

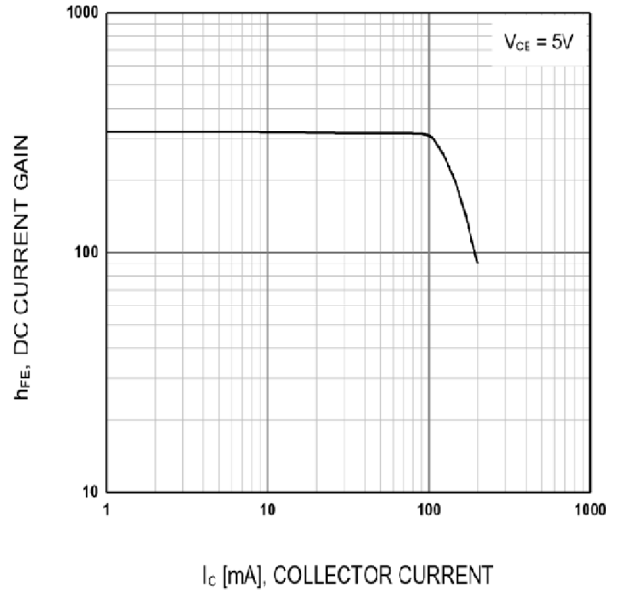
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CB}$ O	$I_C = 100 \mu A , I_E = 0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CE}$ O	$I_C = 1 \text{ mA} , I_B = 0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A , I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 50 \text{ V} , I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 35 \text{ V} , I_B = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3 \text{ V} , I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 5 \text{ V} , I_C = 2 \text{ mA}$	40		450	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 10 \text{ mA} , I_B = 1 \text{ mA}$			0.3	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 10 \text{ mA} , I_B = 1 \text{ mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V} , I_C = 10 \text{ mA} , f = 30 \text{ MHz}$	125			MHz

Typical Characteristics

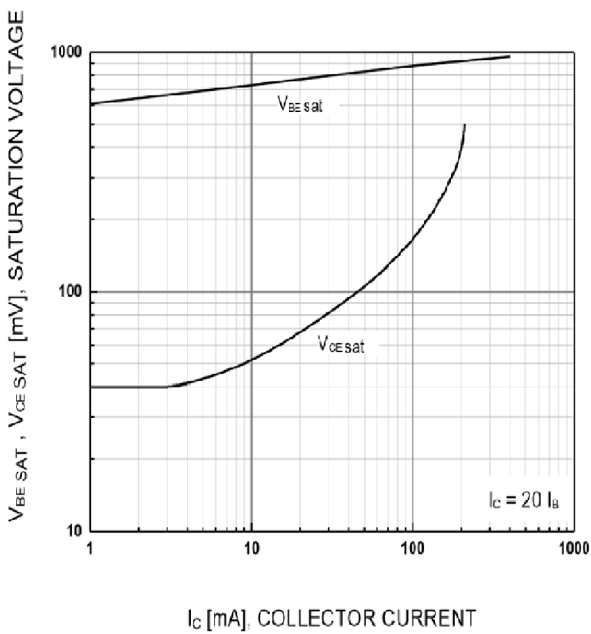
BC347



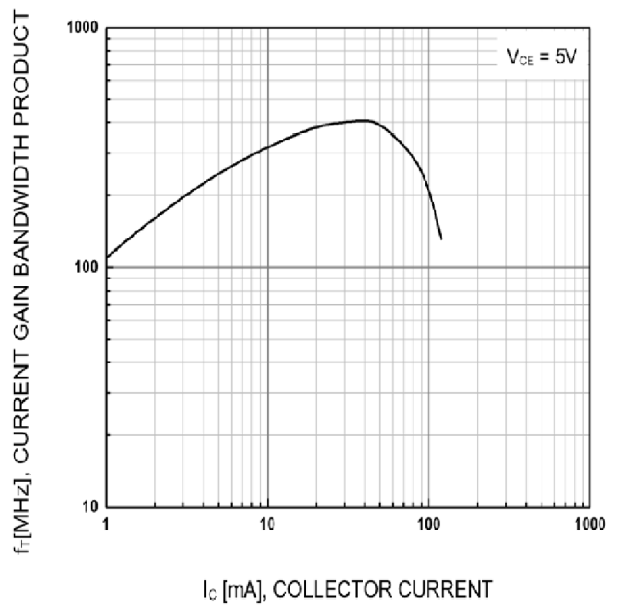
Static Characteristic



DC current Gain



**Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**



Current Gain Bandwidth Product

TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
↓	0.000	0.380	0.000	0.015